

6th Generation 650V/2A SiC Schottky Barrier Diode

Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 150°C
- RoHS compliant



Package Type: SMB



Potential Applications

- Switch mode power supplies

Description

The PS6D060BB SiC Schottky Barrier Diode (SBD) has been developed using Sanan’s advanced 6th generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 650V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V _{RRM}	I _F (135°C)	V _F (25°C)	Q _c	Marking
PS6D060BB	650V	1.3A	1.20V	5.9nC	66BB

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Table 1. Maximum Ratings

(T_c = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V _{RRM}	650	V	T _C = 25°C
Surge peak reverse voltage	V _{RSM}	650		T _C = 25°C
DC reverse voltage	V _{DC}	650		T _C = 25°C
Continuous forward current	I _F	3.9	A	T _C = 25°C
		2		T _C = 115°C
		1.3		T _C = 135°C
Surge non-repetitive forward current	I _{FSM}	15.5	A	T _C = 25°C, t _p = 10ms, half sine pulse
		13		T _C = 150°C, t _p = 10ms, half sine pulse
Surge repetitive forward current	I _{FRM}	13.5	A	T _C = 25°C, t _p = 10ms, half sine wave D = 0.1
Power dissipation	P _{tot}	10.4	W	T _C = 25°C
i ² t value	∫i ² dt	1.2	A ² s	T _C = 25°C, t _p = 10ms
Operating junction temperature	T _j	-55~150	°C	
Storage temperature	T _{stg}	-55~150	°C	

Table 2. Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R _{th(j-c)}	/	12	/	°C/W	

Table 3. Static Electrical Characteristics

(T_j = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V _{DC}	650	/	/	V	I _R = 1mA
Forward voltage	V _F	/	1.20	1.40	V	I _F = 2A, T _j = 25°C
		/	1.40	/		I _F = 2A, T _j = 150°C
Reverse current	I _R	/	35	500	μA	V _R = 650V, T _j = 25°C
		/	250	/		V _R = 650V, T _j = 150°C

Table 4. Dynamic Electrical Characteristics

(T_j = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	131	/	pF	V _R = 0V, f = 1MHz
		/	12	/		V _R = 200V, f = 1MHz
		/	10	/		V _R = 400V, f = 1MHz
Total capacitive charge	Q _C	/	5.9	/	nC	V _R = 400V
Capacitance stored energy	E _C	/	0.9	/	μJ	V _R = 400V

Electrical Characteristic Diagrams

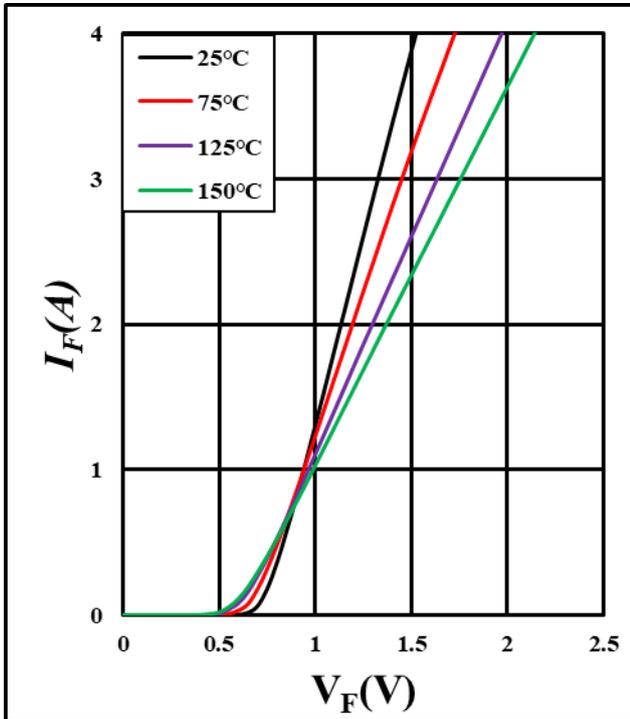


Figure 1. Forward characteristics

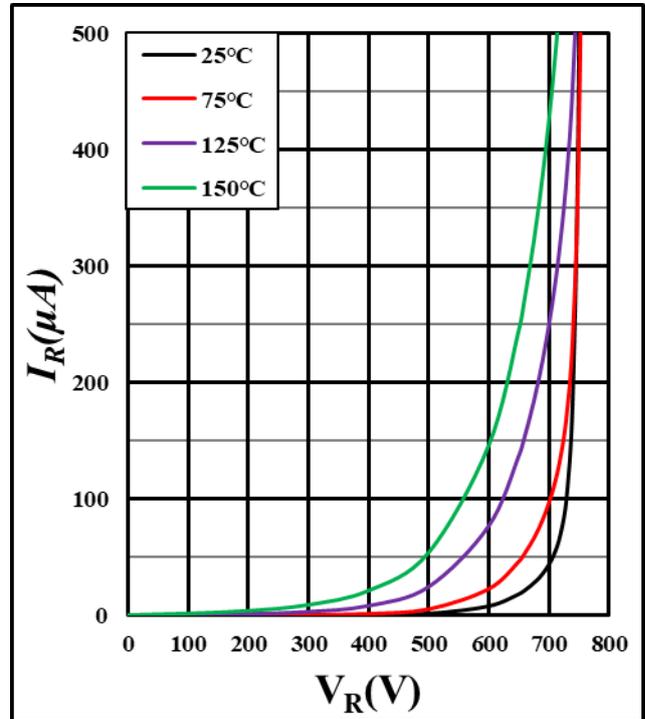


Figure 2. Reverse characteristics

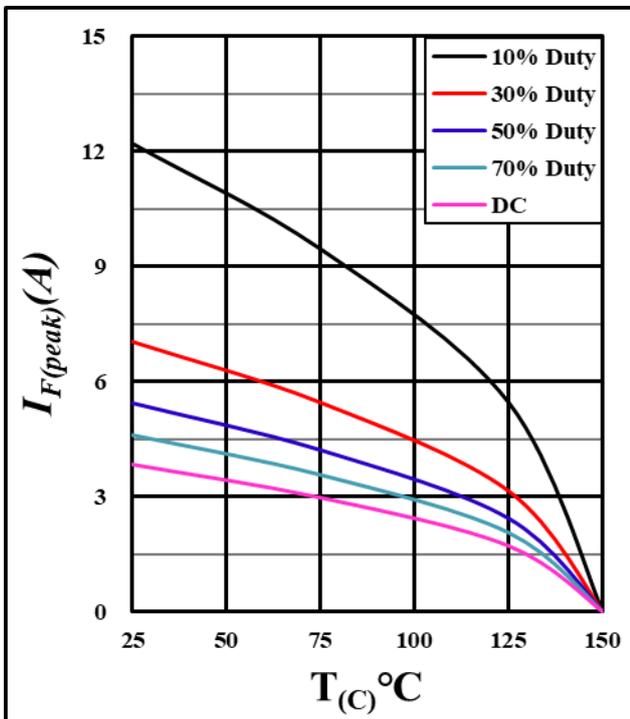


Figure 3. Current derating

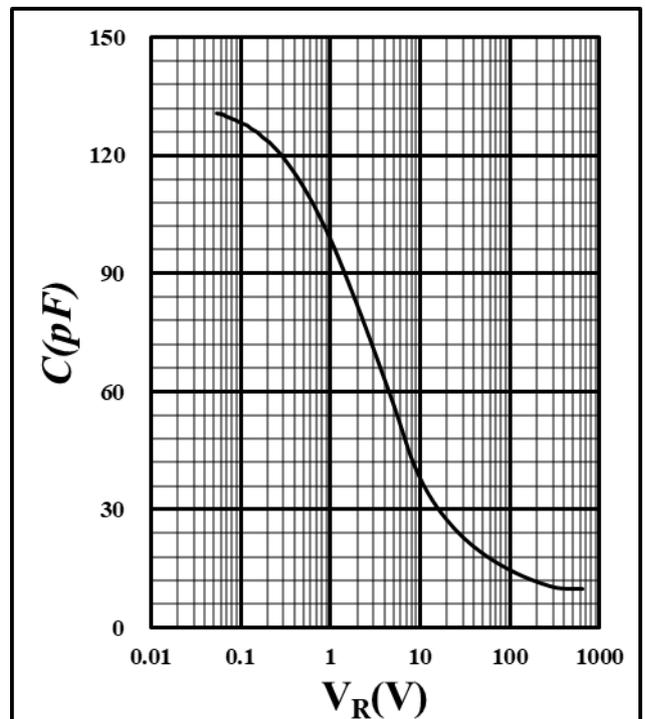


Figure 4. Capacitance vs. reverse voltage

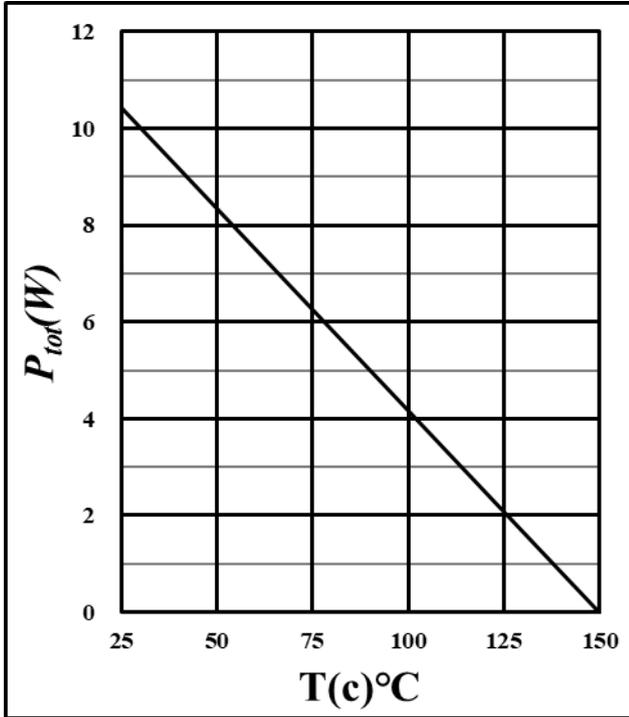


Figure 5. Power derating

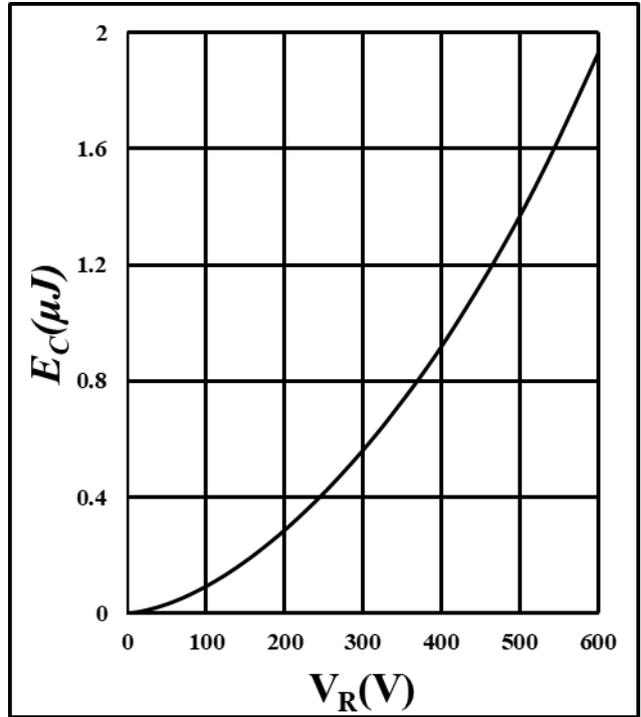


Figure 6. Capacitance stored energy

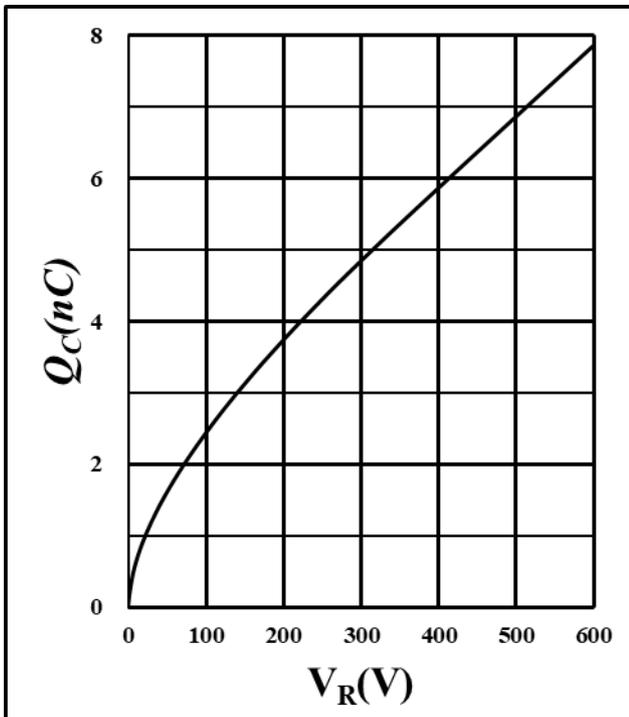
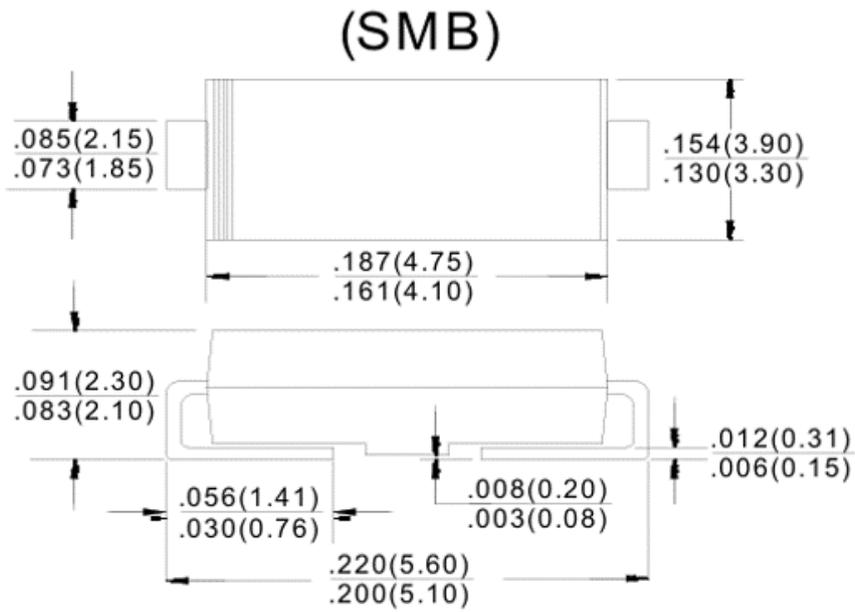


Figure 7. Total capacitance charge vs. reverse voltage

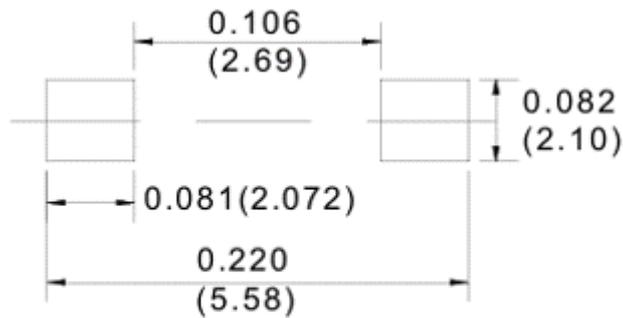
Package Information



Dimensions in inches and (millimeters)

Recommended Solder Pad Layout

Note: All dimensions are in mm



SMB

Ordering Information

Part number	PS6D060BB-CSARH
Package	SMB
Unit quantity	3000 EA
Packing type	Tape & Reel

Important Notices – Read Carefully

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